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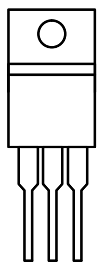
N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A) [a]	Q_g (Typ.)
80	0.0065at V_{GS} = 10 V	80	17.1 nC
	0.0070at V_{GS} = 6.0 V	75	
	0.0085at V_{GS} = 4.5 V	65	

TO-220AB



Top View

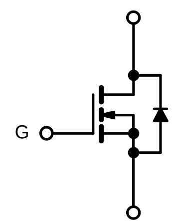
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

RoHS COMPLIANT

APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/AC Inverters
- LED Backlighting



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	80 [a]	A
	T_C = 70 °C		65 [a]	
	T_A = 25 °C		28.6[b, c]	
	T_A = 70 °C		24.9[b, c]	
Pulsed Drain Current (t = 100 μs)		I_{DM}	350	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	80 [a]	
	T_A = 25 °C		4.5[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	30	
Single Pulse Avalanche Energy		E_{AS}	45	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	180	W
	T_C = 70 °C		120	
	T_A = 25 °C		5[b, c]	
	T_A = 70 °C		3.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	0.85	1.1	

Notes

a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.

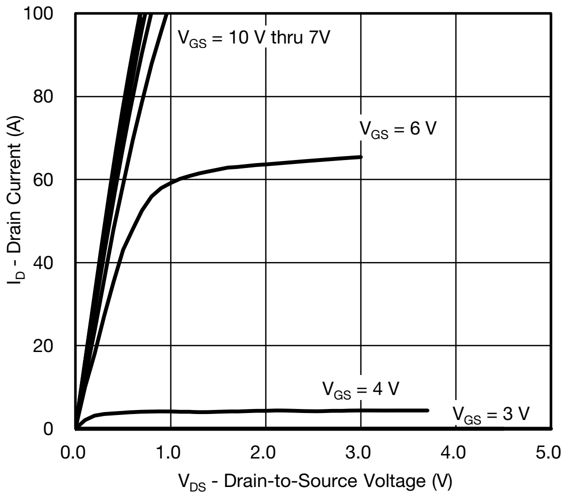
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	80			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 μA		37		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0		3.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	85			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0065		Ω
		V_{GS} = 6 V, I_D = 15 A		0.0070		
		V_{GS} = 4.5 V, I_D = 10 A		0.0085		
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 20 A		60		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		3855		pF
Output Capacitance	C_{oss}			1120		
Reverse Transfer Capacitance	C_{rss}			376		
Total Gate Charge	Q_g	V_{DS} = 40 V,V_{GS} = 10 V, I_D = 10 A		35.5		nC
		V_{DS} = 40 V, V_{GS} = 6 V, I_D = 10 A		22		
		V_{DS} = 40 V,V_{GS} = 4.5 V, I_D = 10 A		18		
Gate-Source Charge	Q_{gs}			5.3		
Gate-Drain Charge	Q_{gd}			7.3		
Output Charge	Q_{oss}	V_{DS} = 40 V, V_{GS} = 0 V		57	86	
Gate Resistance	R_g	f = 1 MHz	0.5	1.3	2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 4 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		12	24	ns
Rise Time	t_r			8	16	
Turn-Off DelayTime	$t_{d(off)}$			32	64	
Fall Time	t_f			7	14	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 4 Ω $I_D \cong$ 10 A, V_{GEN} = 6.0 V, R_g = 1 Ω		14	28	
Rise Time	t_r			11	22	
Turn-Off DelayTime	$t_{d(off)}$			30	60	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			75	A
Pulse Diode Forward Current (t = 100 μs)	I_{SM}				150	
Body Diode Voltage	V_{SD}	I_S = 5 A		0.76	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/μs, T_J = 25 °C		38	75	ns
Body Diode Reverse Recovery Charge	Q_{rr}			36	70	nC
Reverse Recovery Fall Time	t_a			19		ns
Reverse Recovery Rise Time	t_b			19		

Notes

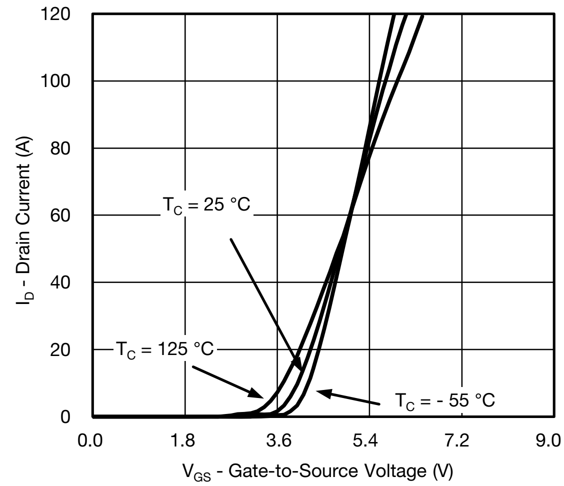
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

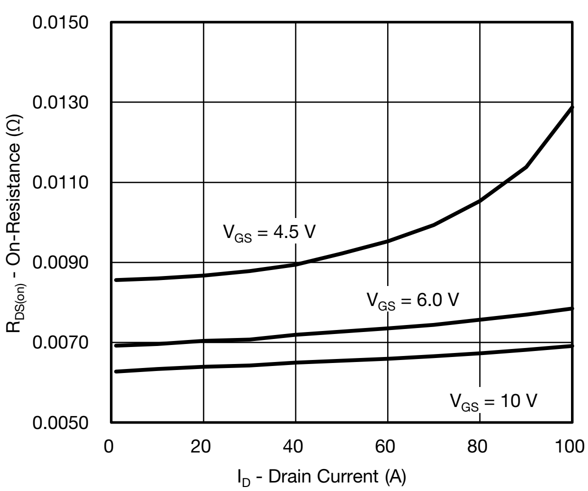
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



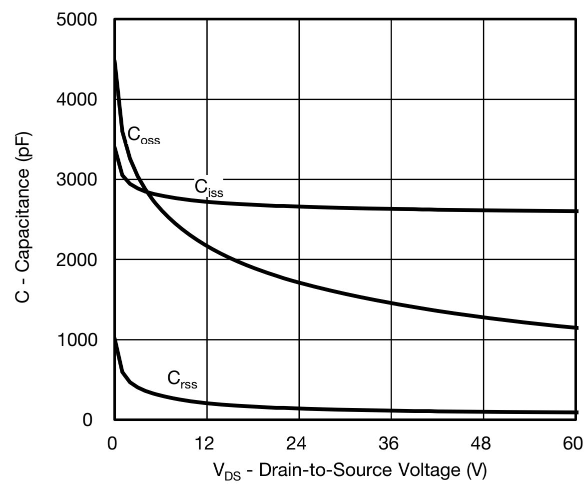
Output Characteristics



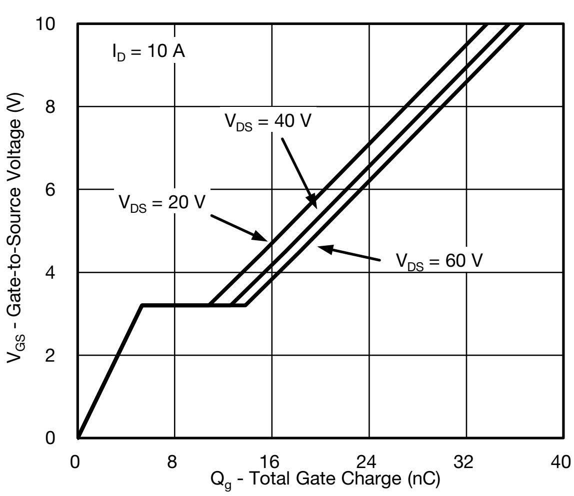
Transfer Characteristics



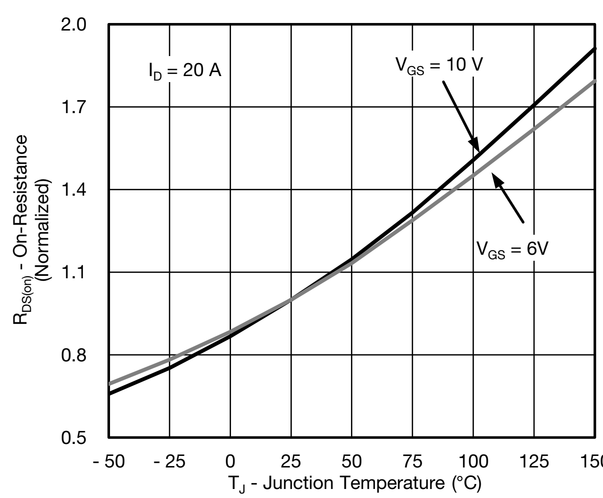
On-Resistance vs. Drain Current



Capacitance

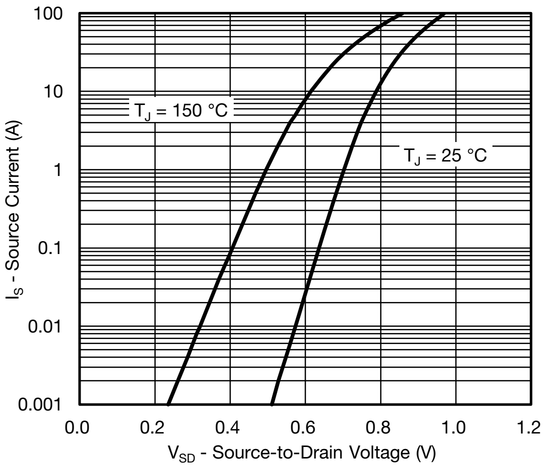


Gate Charge

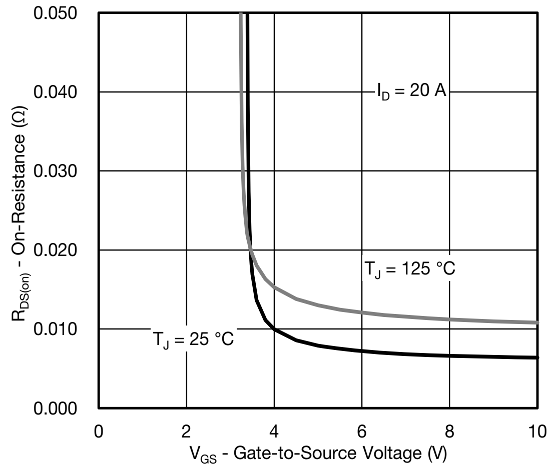


On-Resistance vs. Junction Temperature

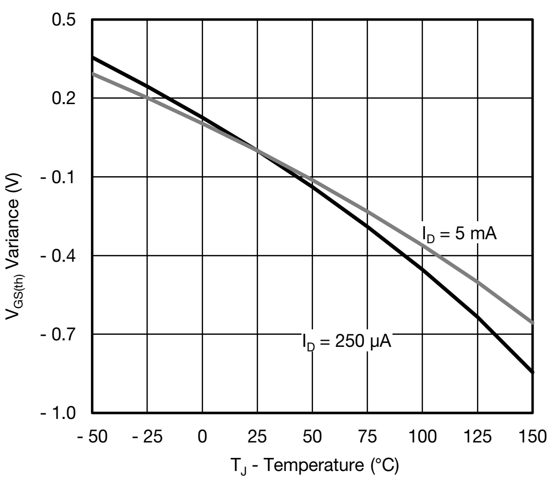
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



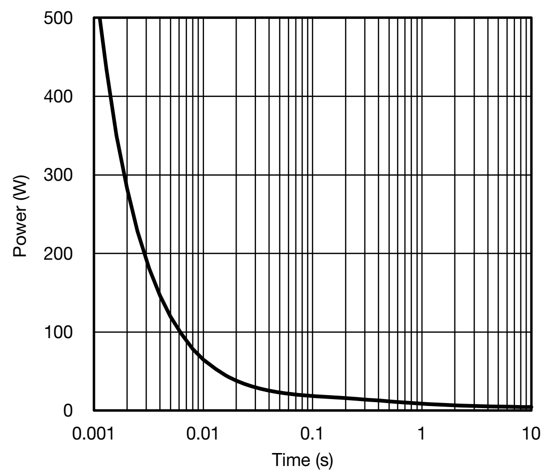
Source-Drain Diode Forward Voltage



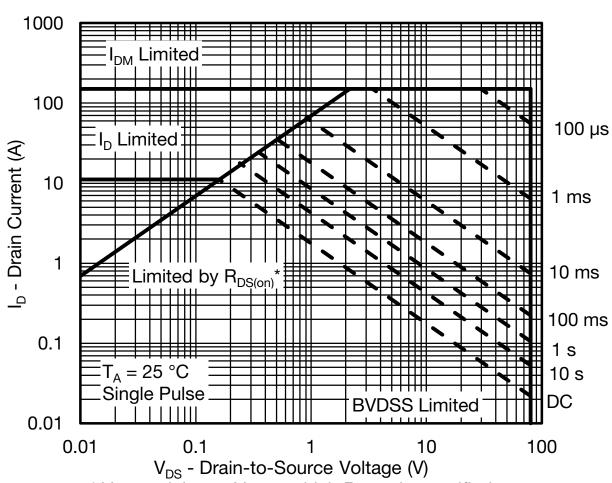
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



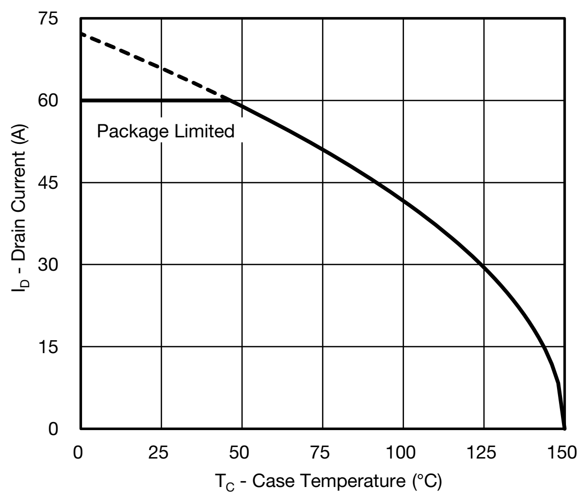
Single Pulse Power, Junction-to-Ambient



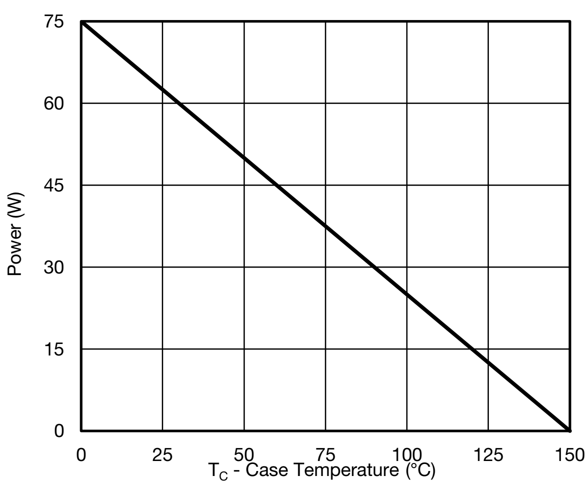
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

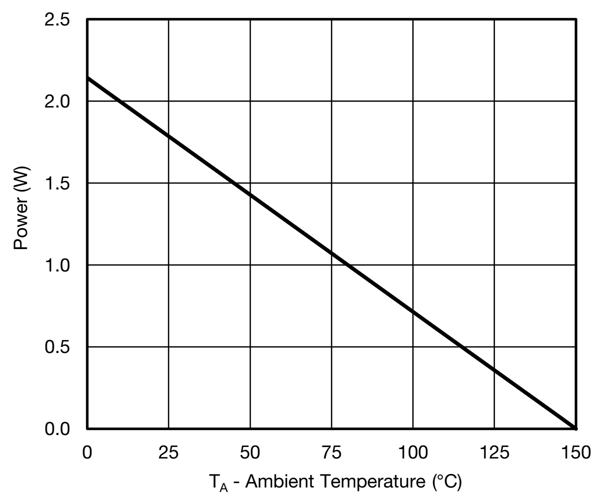
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



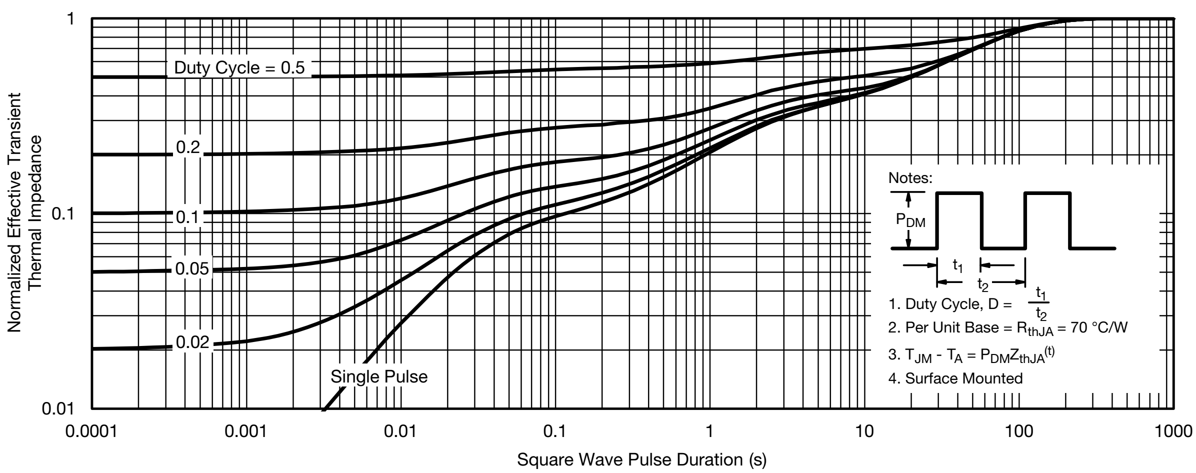
Power, Junction-to-Case



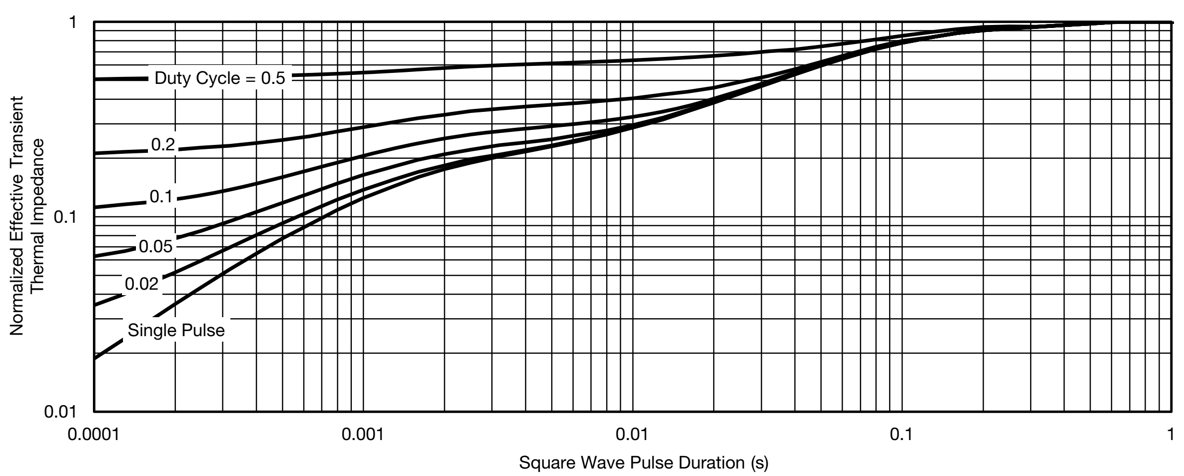
Power, Junction-to-Ambient

** The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.*

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

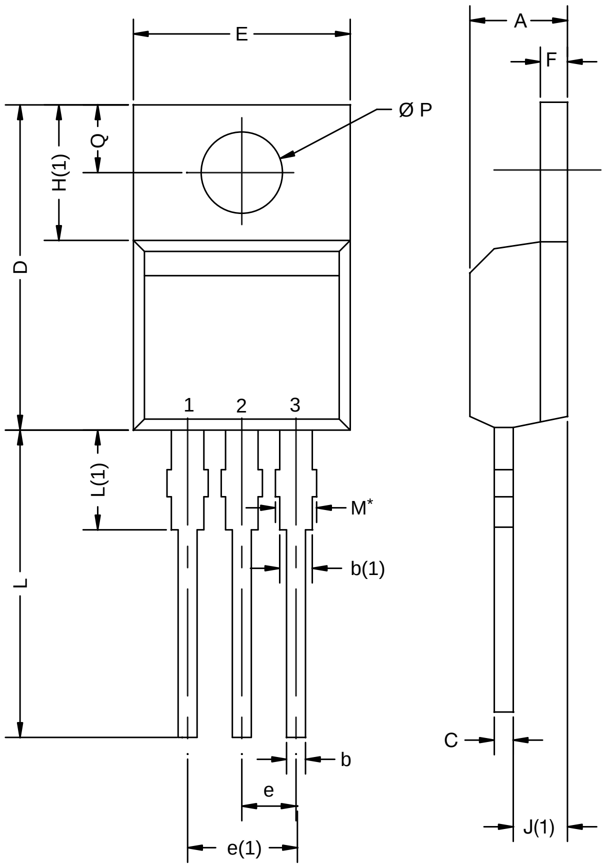


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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